



THE DATASHEET OF SMMBT3904LT1G

MMBT3904L, SMMBT3904L

General Purpose Transistor

NPN Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	40	Vdc
Collector – Base Voltage	V_{CBO}	60	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	200	mAdc
Collector Current – Peak (Note 3)	I_{CM}	900	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

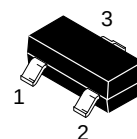
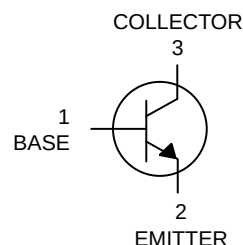
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
3. Reference SOA curve.



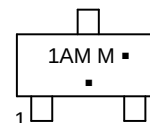
ON Semiconductor®

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SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



1AM = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT3904LT1G SMMBT3904LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT3904LT3G SMMBT3904LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	60	–	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{EB} = 3.0\text{ Vdc}$)	I_{BL}	–	50	nAdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{EB} = 3.0\text{ Vdc}$)	I_{CEX}	–	50	nAdc

ON CHARACTERISTICS (Note 4)

DC Current Gain ($I_C = 0.1\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 50\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$)	H_{FE}	40 70 100 60 30	– – 300 – –	–
Collector – Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	– –	0.2 0.3	Vdc
Base – Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{BE(sat)}$	0.65 –	0.85 0.95	Vdc

SMALL – SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	–	MHz
Output Capacitance ($V_{CB} = 5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	4.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	8.0	pF
Input Impedance ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{ie}	1.0	10	k Ω
Voltage Feedback Ratio ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{re}	0.5	8.0	$\times 10^{-4}$
Small – Signal Current Gain ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{fe}	100	400	–
Output Admittance ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{oe}	1.0	40	μmhos
Noise Figure ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 100\text{ }\mu\text{A}$, $R_S = 1.0\text{ k ohms}$, $f = 1.0\text{ kHz}$)	NF	–	5.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$, $V_{BE} = -0.5\text{ Vdc}$, $I_C = 10\text{ mA}$, $I_{B1} = 1.0\text{ mA}$)	t_d	–	35	ns
Rise Time		t_r	–	35	
Storage Time	$(V_{CC} = 3.0\text{ Vdc}$, $I_C = 10\text{ mA}$, $I_{B1} = I_{B2} = 1.0\text{ mA}$)	t_s	–	200	ns
Fall Time		t_f	–	50	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

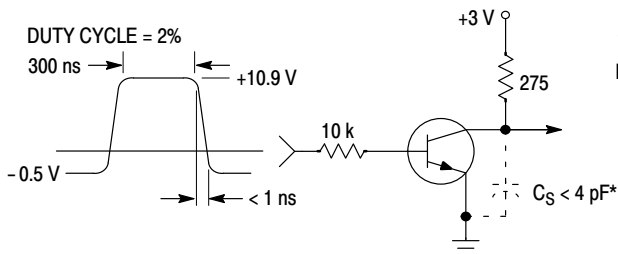


Figure 1. Delay and Rise Time Equivalent Test Circuit

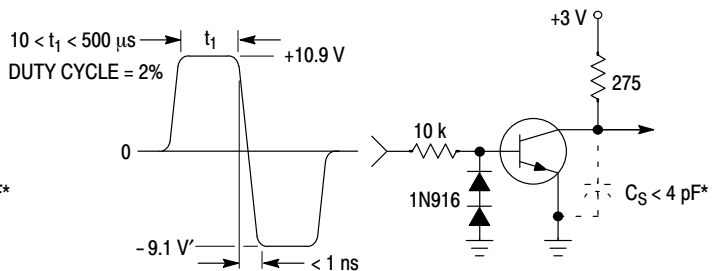


Figure 2. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

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TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
 - - $T_J = 125^\circ\text{C}$

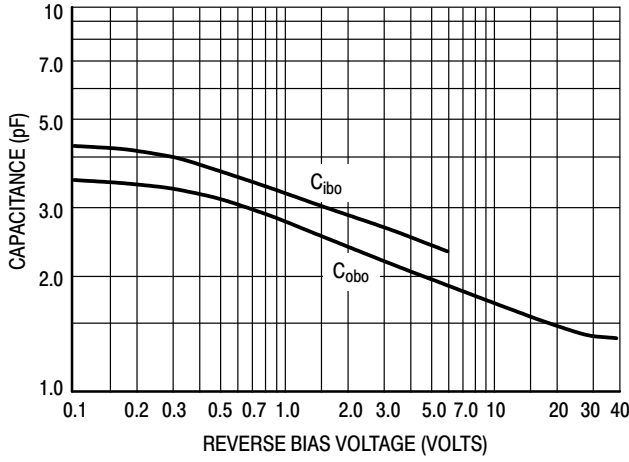


Figure 3. Capacitance

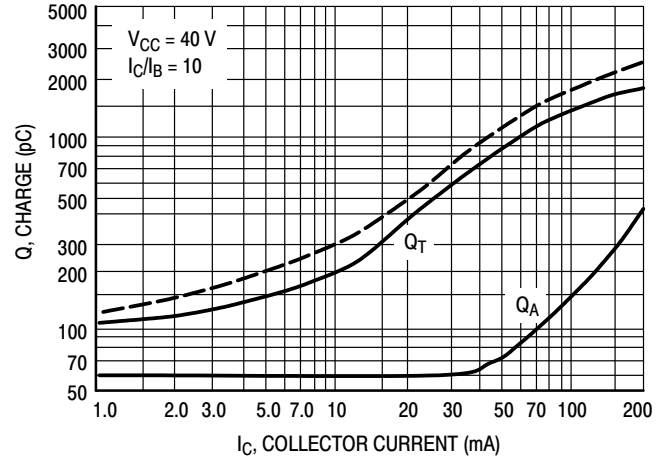


Figure 4. Charge Data

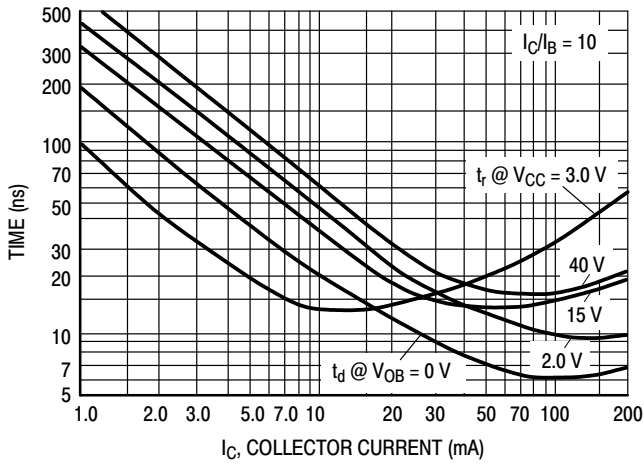


Figure 5. Turn-On Time

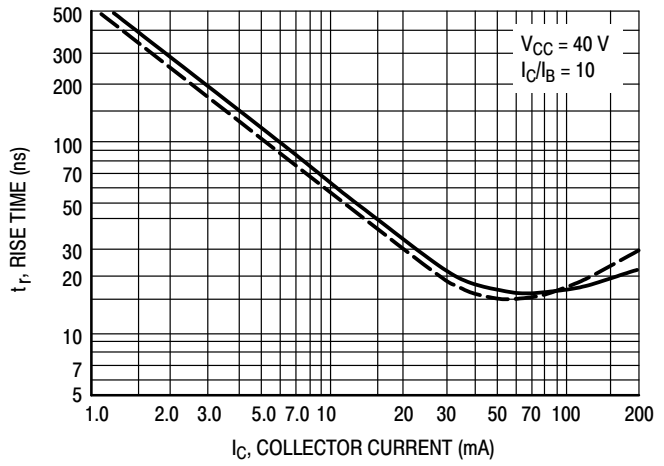


Figure 6. Rise Time

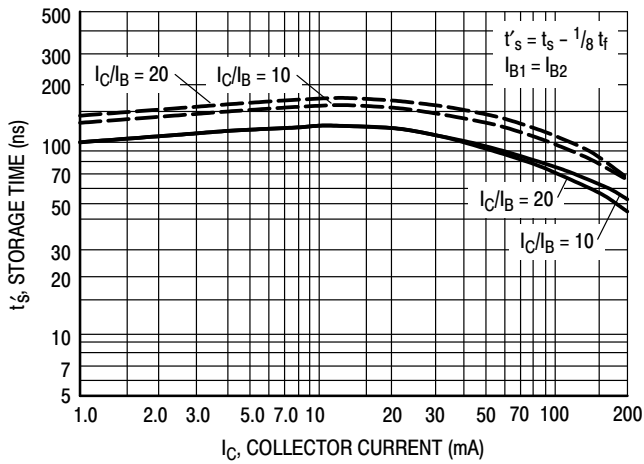


Figure 7. Storage Time

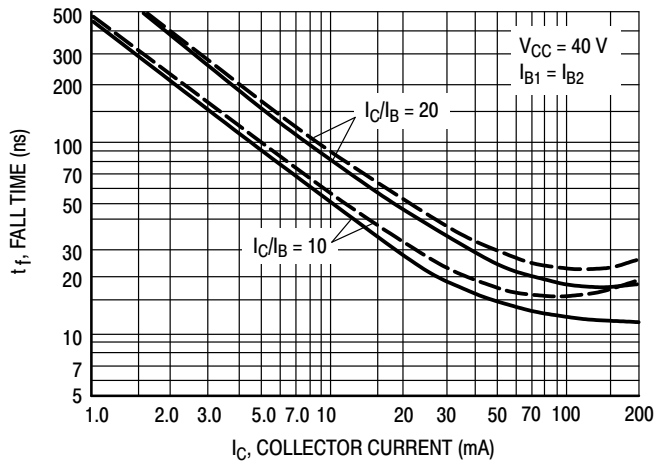


Figure 8. Fall Time

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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

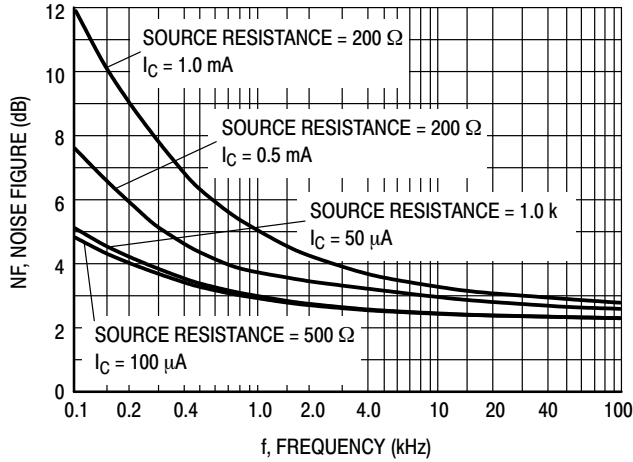


Figure 9.

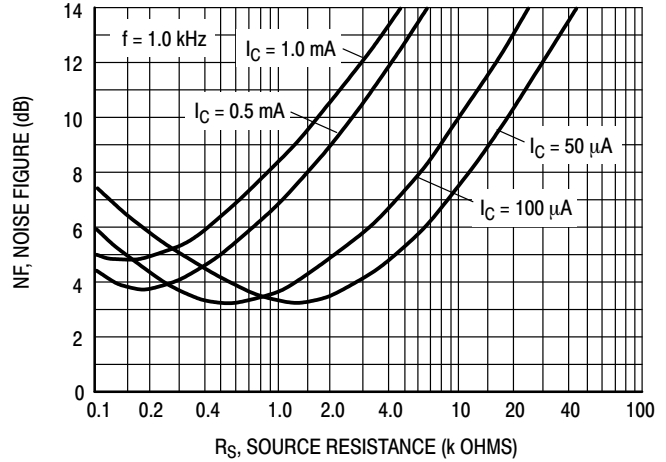


Figure 10.

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

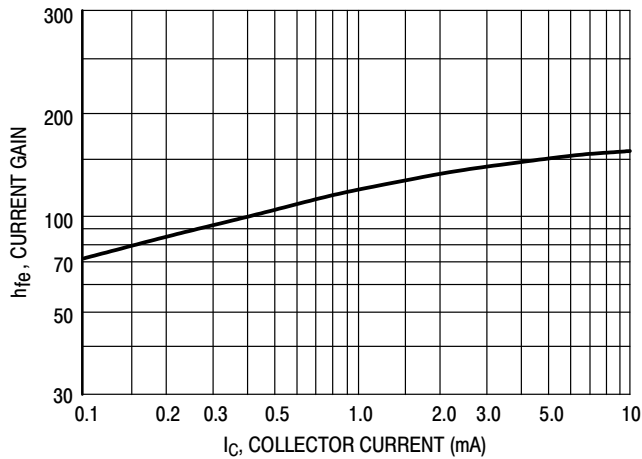


Figure 11. Current Gain

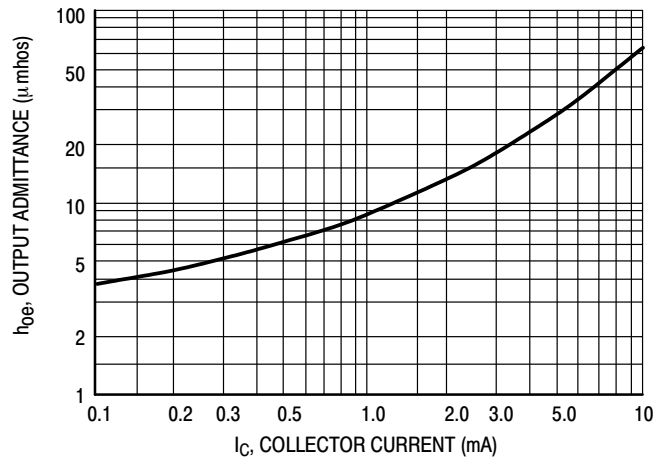


Figure 12. Output Admittance

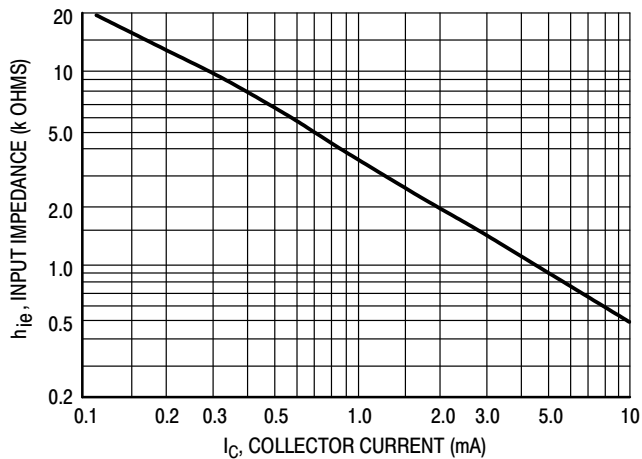


Figure 13. Input Impedance

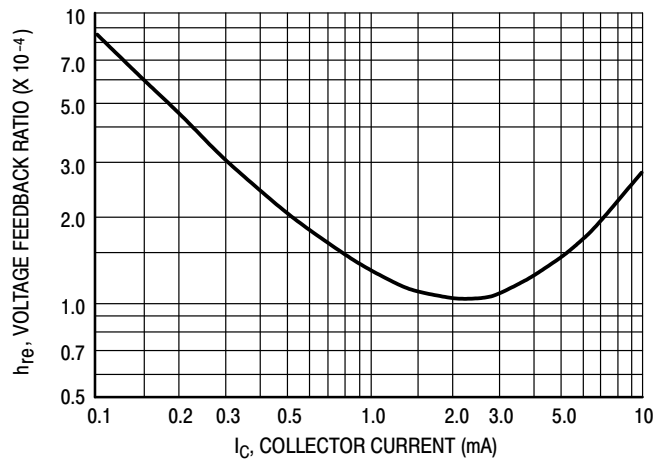


Figure 14. Voltage Feedback Ratio

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TYPICAL STATIC CHARACTERISTICS

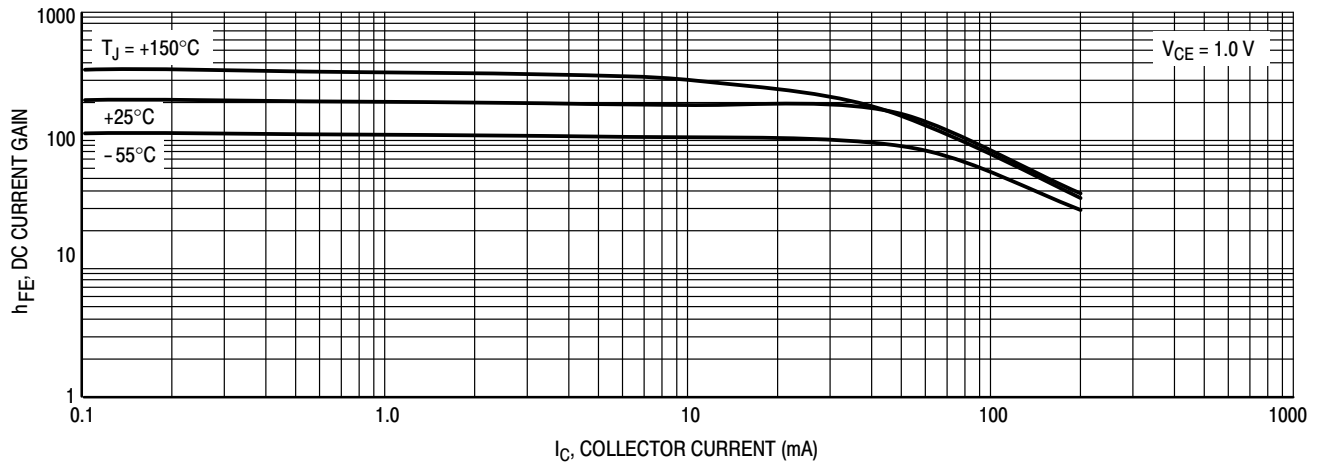


Figure 15. DC Current Gain

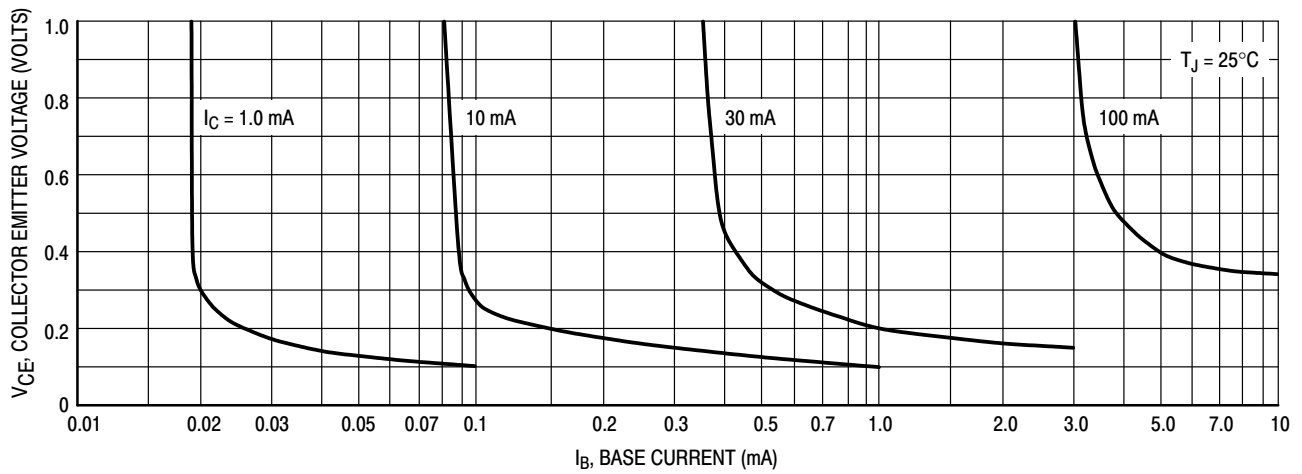


Figure 16. Collector Saturation Region

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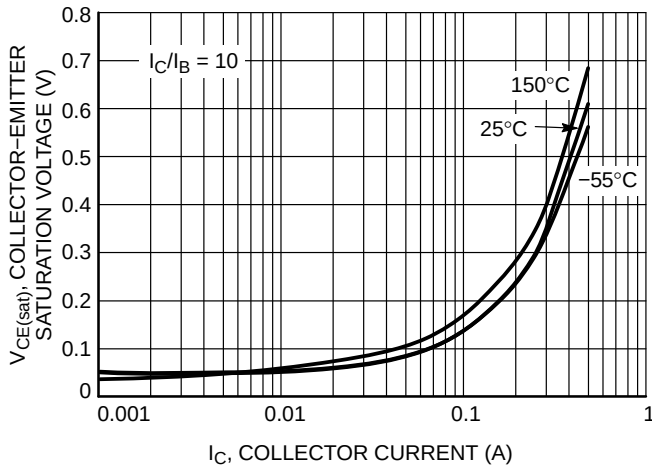


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

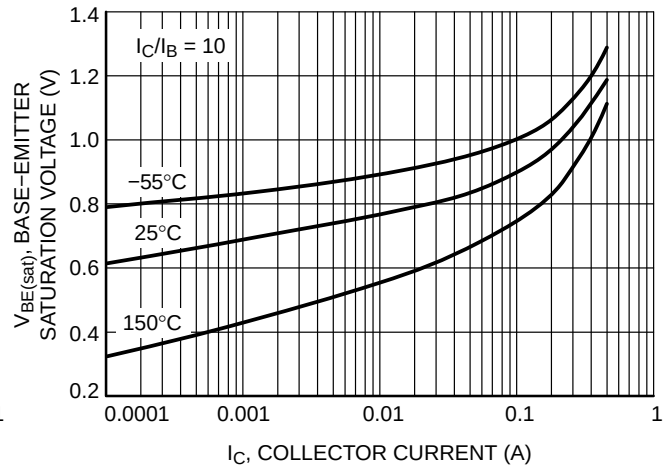


Figure 18. Base Emitter Saturation Voltage vs. Collector Current

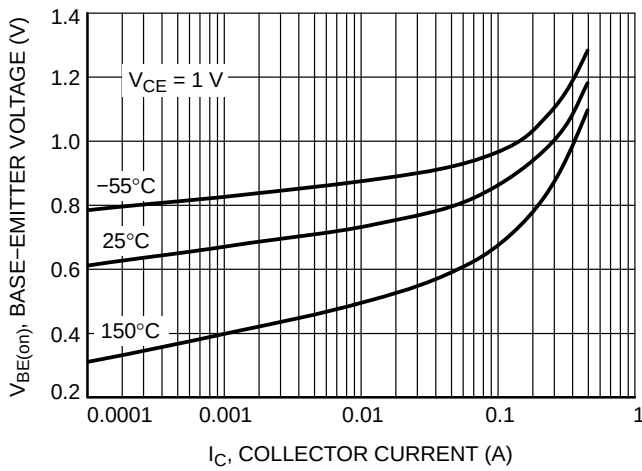


Figure 19. Base Emitter Voltage vs. Collector Current

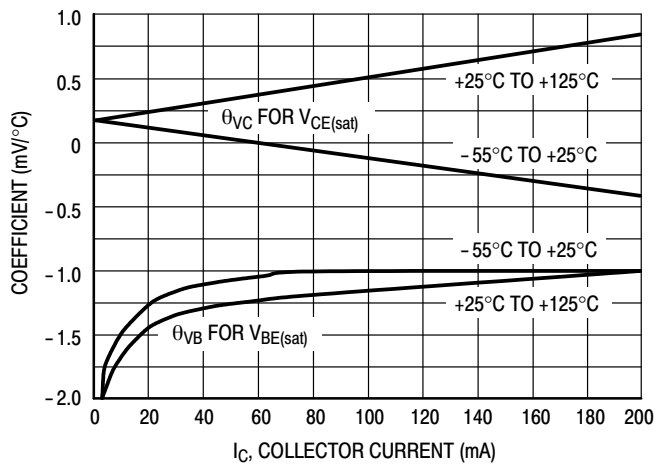


Figure 20. Temperature Coefficients

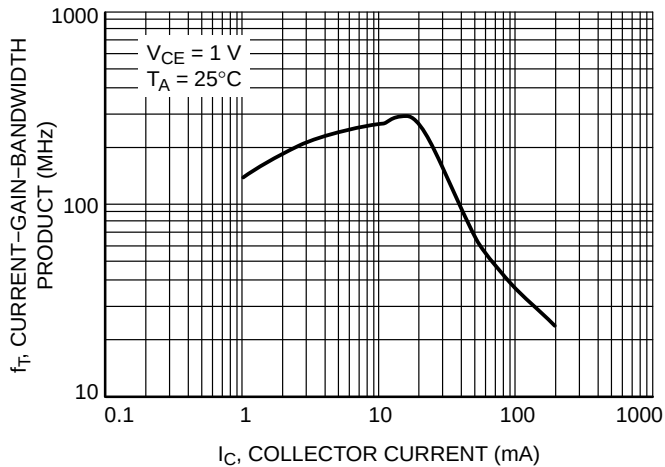


Figure 21. Current Gain Bandwidth vs. Collector Current

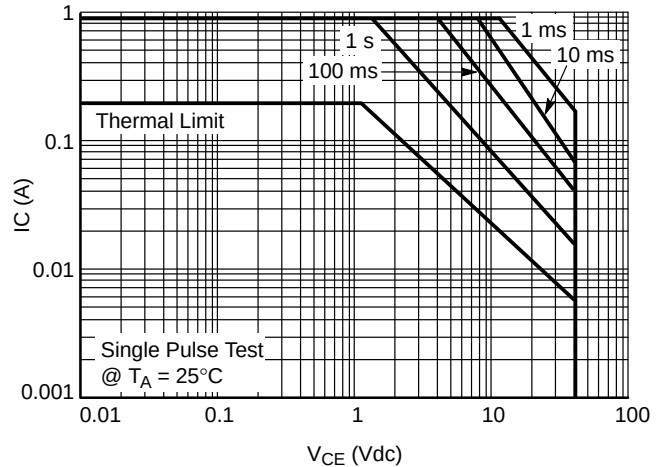
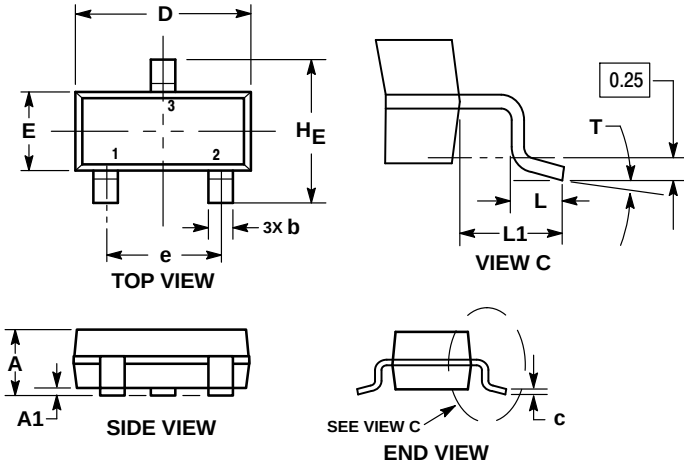


Figure 22. Safe Operating Area

MMBT3904L, SMMBT3904L

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR

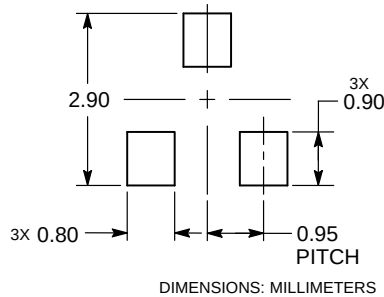


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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